Abstracts

A 4 GHz High Power Transistor - Design and Reliability

P. Wang, J. Chen, P. Froess and S. Kakihana. "A 4 GHz High Power Transistor - Design and Reliability." 1973 G-MTT International Microwave Symposium Digest of Technical Papers 73.1 (1973 [MWSYM]): 236-238.

An experimental high power, high gain 4 GHz transistor is described. The design aspects of high breakdown voltage, ballasting resistors, metallization system and thermal design are reviewed. It is shown how these consideration have been optimized for device reliability and long MTF.

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